

Dongri Qiu

List of Publications by Year in descending order

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Version: 2024-02-01

18
papers

297
citations

840776

11
h-index

996975

15
g-index

18
all docs

18
docs citations

18
times ranked

637
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrically Tunable and Negative Schottky Barriers in Multi-layered Graphene/MoS ₂ Heterostructured Transistors. Scientific Reports, 2015, 5, 13743.	3.3	55
2	Toward negligible charge loss in charge injection memories based on vertically integrated 2D heterostructures. Nano Research, 2016, 9, 2319-2326.	10.4	36
3	Structural and optical characterization of MoS ₂ quantum dots defined by thermal annealing. Journal of Luminescence, 2017, 183, 62-67.	3.1	29
4	Enhancement of near-infrared detectability from InGaZnO thin film transistor with MoS ₂ light absorbing layer. Nanotechnology, 2017, 28, 475206.	2.6	26
5	Selective control of electron and hole tunneling in 2D assembly. Science Advances, 2017, 3, e1602726.	10.3	25
6	Locally Gated SnS ₂ /hBN Thin Film Transistors with a Broadband Photoresponse. Scientific Reports, 2018, 8, 10585.	3.3	21
7	Electrical and photovoltaic properties of residue-free MoS ₂ thin films by liquid exfoliation method. Nanotechnology, 2017, 28, 195703.	2.6	18
8	Structural and optical properties of MoS ₂ layers grown by successive two-step chemical vapor deposition method. Thin Solid Films, 2015, 587, 47-51.	1.8	16
9	Formation of transition metal dichalcogenides thin films with liquid phase exfoliation technique and photovoltaic applications. Solar Energy Materials and Solar Cells, 2018, 184, 9-14.	6.2	16
10	Transport properties of unrestricted carriers in bridge-channel MoS ₂ field-effect transistors. Nanoscale, 2015, 7, 17556-17562.	5.6	14
11	High photoresponsivity from multilayer MoS ₂ /Si heterojunction diodes formed by vertically stacking. Journal of Applied Physics, 2017, 122, .	2.5	11
12	Recent Advances in Synthesis and Assembly of van der Waals Materials. Journal of the Korean Physical Society, 2018, 73, 805-816.	0.7	11
13	Hole Conduction of Tungsten Diselenide Crystalline Transistors by Niobium Dopant. Advanced Electronic Materials, 2019, 5, 1800695.	5.1	7
14	Room temperature ferromagnetic and ambipolar behaviors of MoS ₂ doped by manganese oxide using an electrochemical method. Applied Physics Letters, 2017, 110, .	3.3	7
15	Semiconducting properties of perchlorate-doped graphene using an electrochemical method. RSC Advances, 2017, 7, 16823-16825.	3.6	4
16	Controllable Growth of Single Layer MoS ₂ and Resistance Switching Effect in Polymer/MoS ₂ Structure. Applied Science and Convergence Technology, 2017, 26, 129-132.	0.9	1
17	Resistive switching memory device with metal oxide quantum dots on a graphene layer. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 325-328.	1.8	0
18	Room temperature ferromagnetic and semiconducting properties of graphene adsorbed with cobalt oxide using electrochemical method. Journal of Magnetism and Magnetic Materials, 2017, 444, 361-363.	2.3	0